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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of )  
Chan-ho PARK )  
Serial No. 10/024475 ) Examiner: Junghwa M. IM  
Filed: December 21, 2001 ) Group Art Unit: 2811  
For: HIGH VOLTAGE SEMICONDUCTOR DEVICE HAVING HIGH BREAKDOWN  
VOLTAGE AND METHOD OF FABRICATING THE SAME

INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

Under the provisions of 37 C.F.R. §§ 1.56, 1.97 and 1.98,  
Applicant submits herewith copies of publications that the Office  
may wish to consider in examination of the subject application.  
The publications are listed on the attached form PTO-1449.

The relevance of any foreign-language reference for which an  
English-language translation is not provided is as follows.

JP 4-323832 has been cited in an Office Action issued by the  
Korean Patent Office during examination of the corresponding  
Korean application.

I hereby certify that each item of information contained in  
this information disclosure statement was first cited in a

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communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

Respectfully submitted,

By



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Application Number	10/024475
Filing Date	December 21, 2001
First Named Inventor	Chan-ho PARK
Group Art Unit	2811
Examiner Name	Junghwa M. IM

Attorney Docket Number | 1751-294

[illegible]

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee of Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T°
		Office <sup>3</sup> Code	Number <sup>4</sup>	Kind <sup>5</sup> (if known)			
	1	JP	4-323832 (abstract attached)		MITSUBISHI ELECTRIC CORP	11/13/1992	

Examiner Signature		Date Considered	
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<sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two-letter code. <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language translation is attached. AB indicates that only an English language abstract is attached.